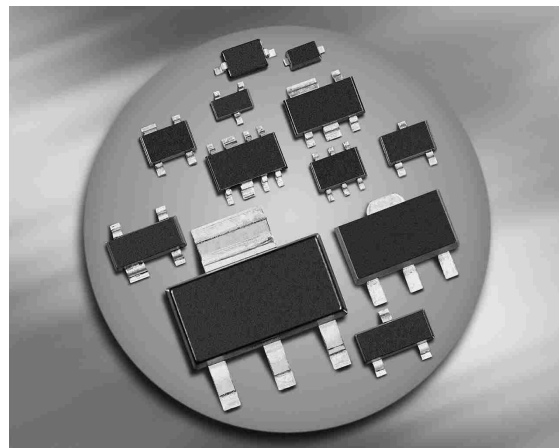
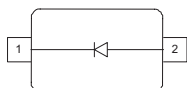


Silicon Tuning Diode

- For SAT - Indor units
- High capacitance ratio C_{1V}/C_{25V} (typ.15.8)
- Low series inductance
- Excellent uniformity and matching due to "in-line" matching assembly procedure



BB867-02V



Type	Package	Configuration	L_S (nH)	Marking
BB867-02V*	SC79	single	0.6	Y

* Preliminary

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage- ($R \geq 5\text{k}\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 30\text{ V}$ $V_R = 30\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$	I_R	- - -	- - -	10 200	nA
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	8 0.5 0.45	8.7 0.55 0.52	9.4 0.6 -	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T25}	14	15.8	-	-
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	-	16.7	-	
Capacitance matching ¹⁾ $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	5	%
Series resistance $V_R = 5\text{ V}, f = 470\text{ MHz}$	r_S	-	2.8	-	Ω

¹For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

